

**THE FOLLOWING ARE THE ENGLISH TRANSLATION
OF ANNEXES TO THE INTERNATIONAL PRELIMINARY
EXAMINATION REPORT (ARTICLE 34):**

Amended Sheet (Page 10)

CLAIMS

1. (Amended) A method for growing a thin nitride film over a sapphire substrate, comprising carrying out a low temperature process comprising the steps of subjecting the sapphire substrate to H₂ cleaning and treating the cleaned sapphire substrate with an acidic solution to thereby control the polarity of the thin nitride film.

2. (Amended) The method for growing a thin nitride film over a substrate according to claim 1, further comprising exposing the sapphire substrate to an outside air before the growth of the thin nitride film over the sapphire substrate.

3. (Amended) The method for growing a thin nitride film over a substrate according to claim 1, wherein the acidic solution is nitric acid.

4. The method for growing a thin nitride film over a substrate according to claim 1, comprising the steps of subjecting the substrate to H₂ cleaning, forming a mask, and treating the cleaned substrate with a solution through the mask to thereby form patterned regions having different polarities in the thin nitride film.

5. A thin nitride film device formed by the method for growing a thin nitride film over a substrate according to claim 1.

6. The thin nitride film device according to claim 5, comprising a c face sapphire (Al₂O₃) substrate, a Ga face and